

50V P-CHANNEL ENHANCEMENT MODE FIELD-EFFECT TRANSISTOR

Product Summary

BV_{DS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
-50V	10Ω @ $V_{GS} = -5V$	-164mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- General-purpose interfacing switches
- Power-management functions
- Analog switches

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The BSS84WQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
<https://www.diodes.com/quality/product-definitions/>

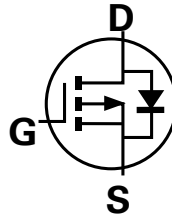
Mechanical Data

- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe). Ⓔ③
- Weight: 0.006 grams (Approximate)

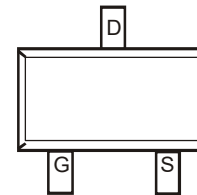
SOT323



Top View



Equivalent Circuit



Top View

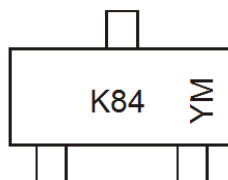
Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
BSS84WQ-7-F	SOT323	3,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT323



K84 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: N = 2026)
M = Month (ex: 9 = September)

Date Code Key

Year	2020	-	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035
Code	H	-	N	P	R	S	T	U	V	W	X	Y

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

BSS84WQ

Document number: DS43027 Rev. 3 - 2

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June 2026
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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-50	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-164 -131	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-164	mA
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)			I _{DM}	-800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	330	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	388	°C/W
Total Power Dissipation (Note 6)			P _D	410	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	307	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	—	V	V _{GS} = 0, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -50V, V _{GS} = 0, T _J = +25°C
		—	—	-2	μA	V _{DS} = -50V, V _{GS} = 0, T _J = +125°C (Note 8)
		—	—	-100	nA	V _{DS} = -25V, V _{GS} = 0, T _J = +25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.8	-1.6	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.1	10	Ω	V _{GS} = -5V, I _D = -0.1A
Forward Transconductance	g _{FS}	0.05	—	—	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0, f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A,
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	R _{GEN} = 50Ω, V _{GS} = -10V

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 - Short duration pulse test used to minimize self-heating effect.
 - Guarantee by design. Not subject to production testing.

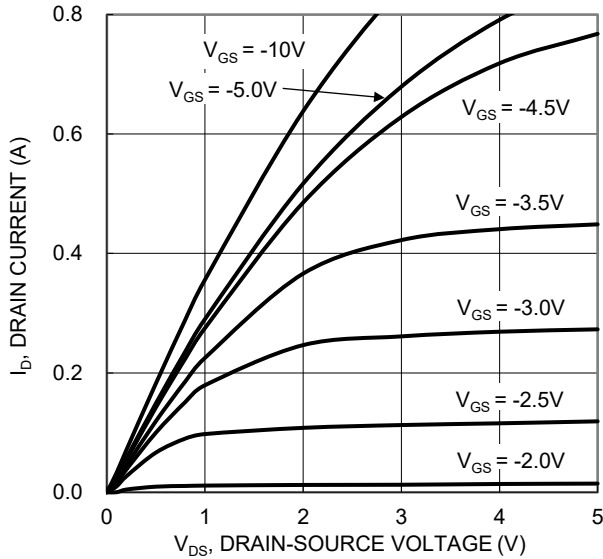


Figure 1. Typical Output Characteristic

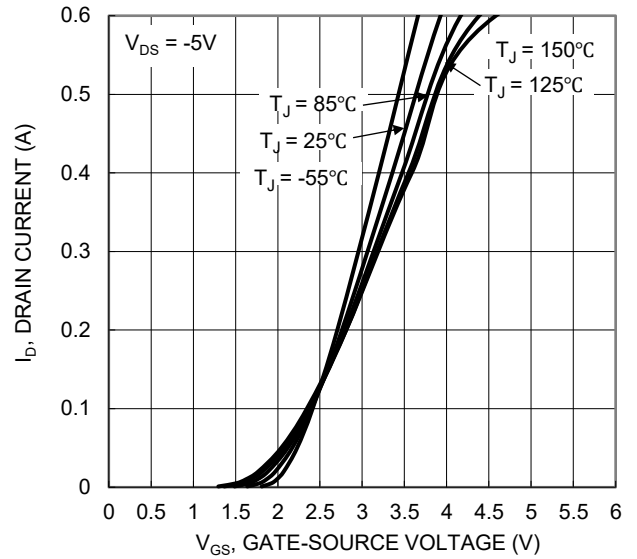


Figure 2. Typical Transfer Characteristic

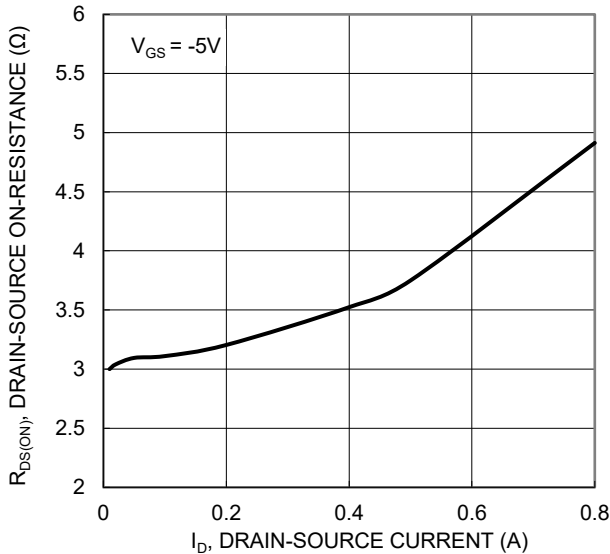


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

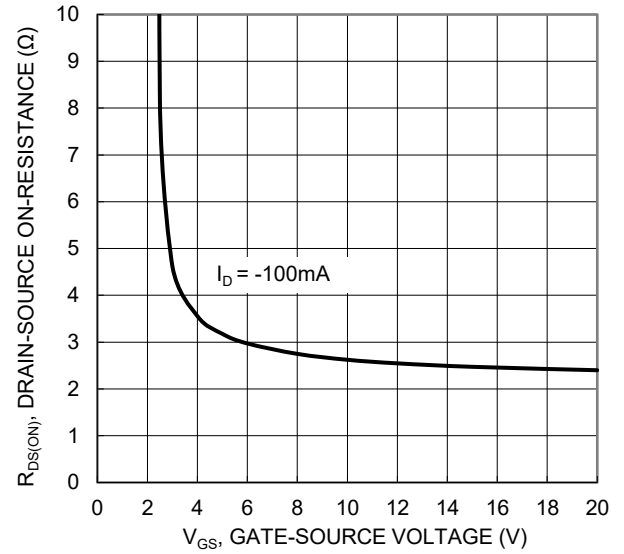


Figure 4. Typical Transfer Characteristic

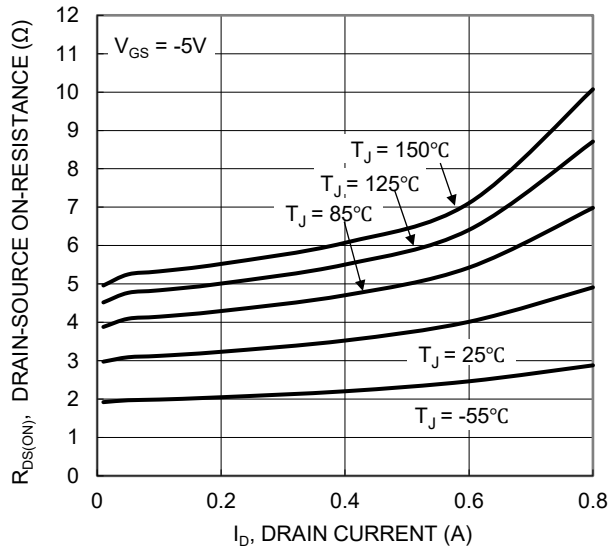


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

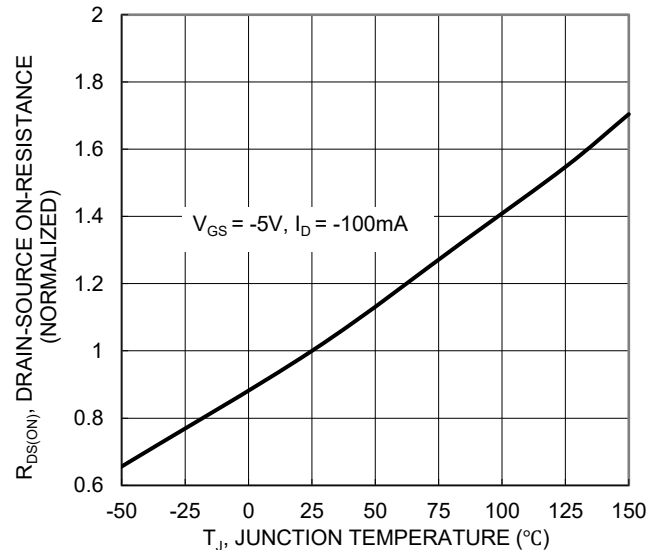


Figure 6. On-Resistance Variation with Junction Temperature

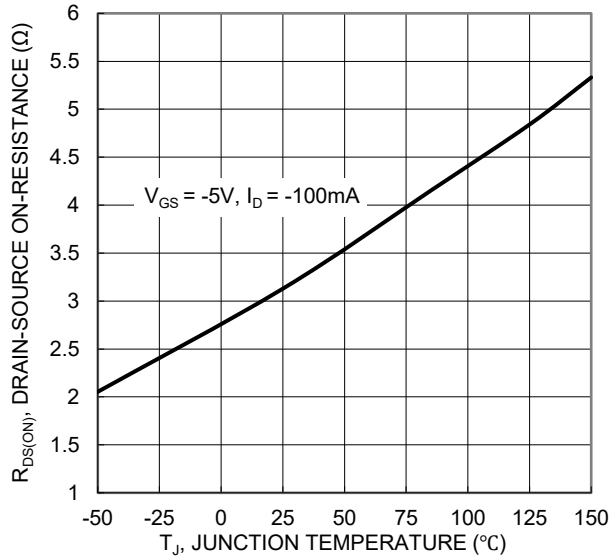


Figure 7. On-Resistance Variation with Junction Temperature

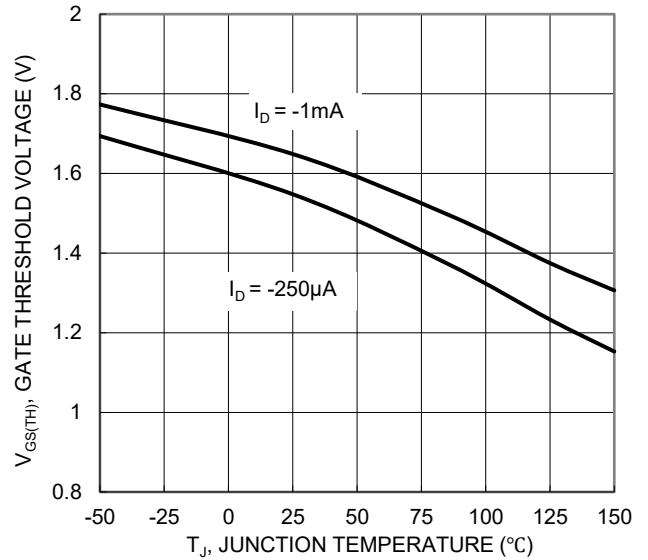


Figure 8. Gate Threshold Variation vs. Junction Temperature

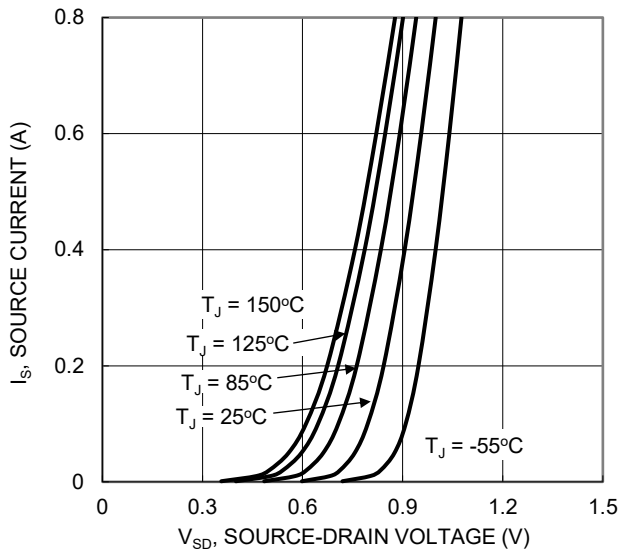


Figure 9. Diode Forward Voltage vs. Current

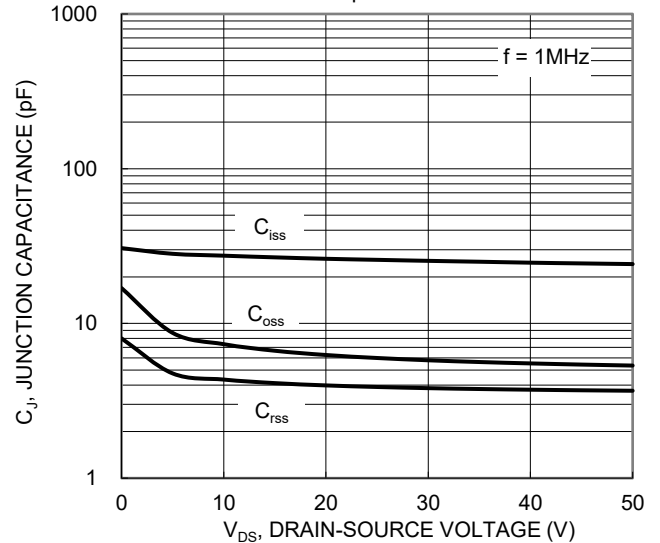


Figure 10. Typical Junction Capacitance

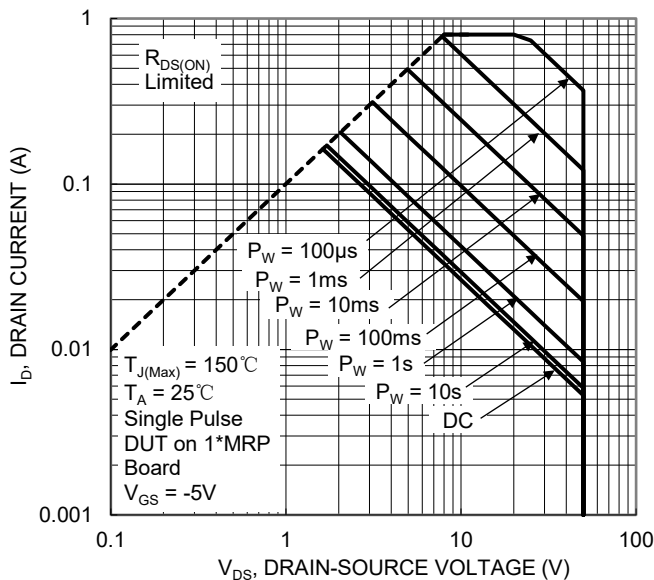
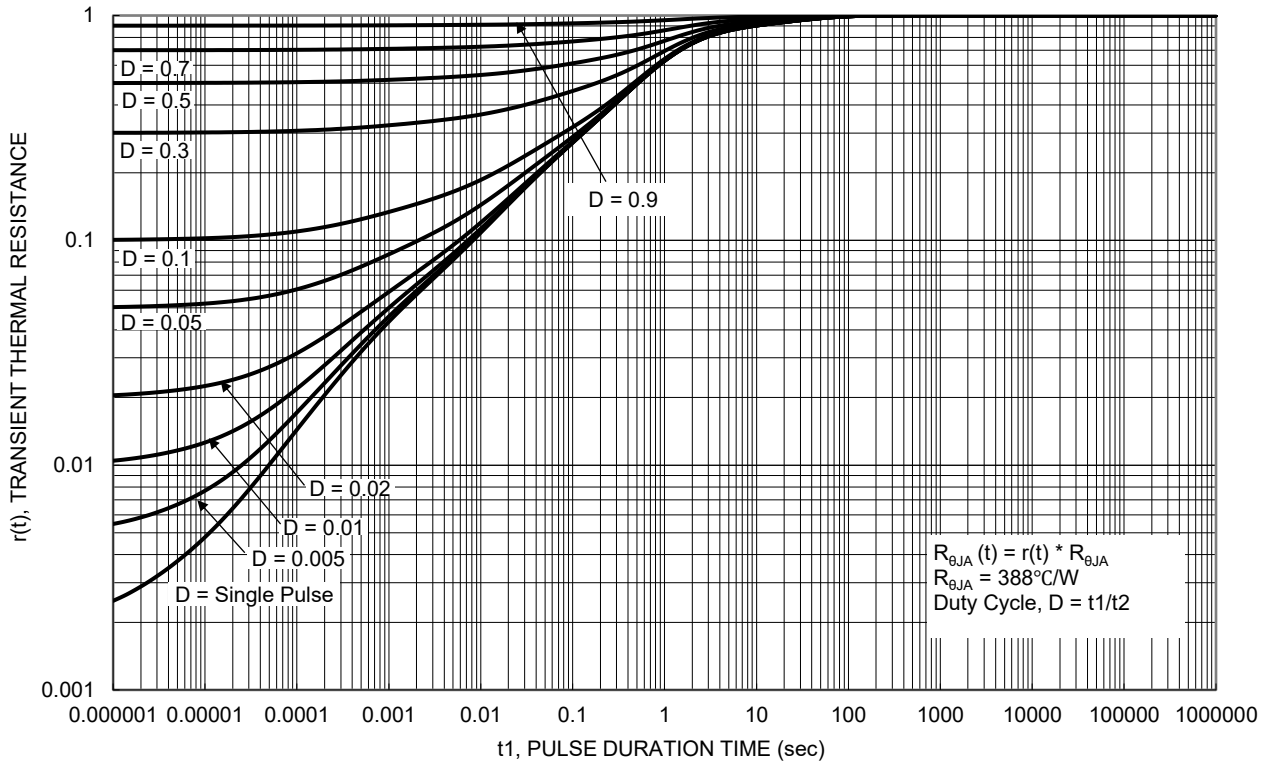


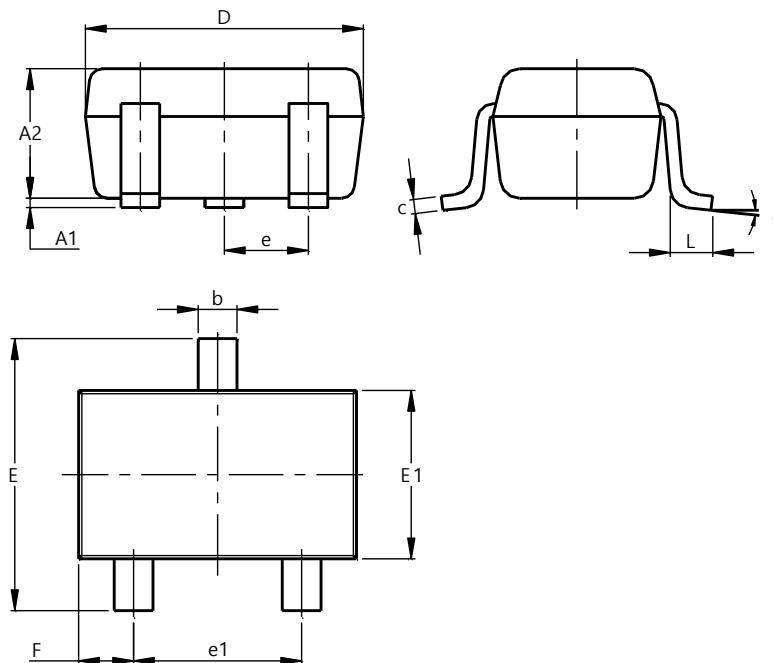
Figure 11. SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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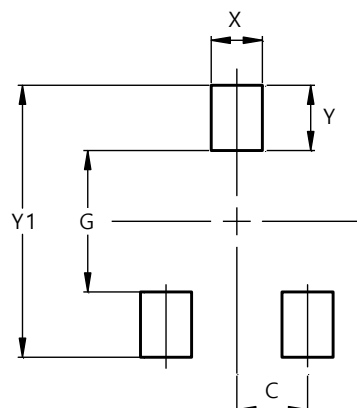


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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